

5. The etching method according to claim 2, wherein the etching gas supply rate is 8.4 sccm to 16.9 sccm for a substantial volume of one liter of the reaction chamber.

6. The etching method according to claim 3, wherein the etching gas supply rate is 8.4 sccm to 16.9 sccm for a substantial volume of one liter of the reaction chamber.

7. The etching method according to claim 1, wherein a flow of etchant is provided at a flow rate which produces a flow rate diverging position with respect to an outer periphery of an object being etched that is substantially at or internal to the outer periphery of the object being etched.

8. The etching method according to claim 2, wherein a flow of etchant is provided at a flow rate which produces a flow rate diverging position with respect to an outer periphery of an object being etched that is substantially at or internal to the outer periphery of the object being etched.

9. The etching method according to claim 3, wherein a flow of etchant is provided at a flow rate which produces a flow rate diverging position that is internal to an outer periphery of an object being etched.

10. The etching method according to claim 4, wherein a flow of etchant is provided at a flow rate which produces a flow rate diverging position that is internal to an outer periphery of an object being etched.

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11. The etching method according to claim 1 wherein the process pressure is about 5 to about 10 mTorr.

12. The etching method according to claim 11 wherein the process pressure is 5mTorr.

13. The etching method according to claim 4 wherein the process pressure is about 5 to about 10 mTorr.

14. The etching method according to claim 7 wherein the process pressure is about 5 to about 10 mTorr.

REMARKS

Reconsideration of the Office Action of November 15, 1999 is respectfully requested. Enclosed herewith is a one month petition for extension of time together with the requisite fee.

In the above amendments, new claims 4 to 14 have been added, with claims 1-3 remaining as originally presented. With respect to new claims 4-14, support for the subject matter of new claim 4 (which is similar to that added in claims 5 and 6) can be found in the disclosure and illustration setting forth tested points of 500 sccm and 1000 sccm with the former representing about 8.4 (500/59 l) sccm per substantial liter of the reaction chamber and the latter about 16.9 sccm (1000/59 l) per substantial liter of reaction chamber. (See In re Wetheim 191 USPQ 96, 98 (C.C.P.A. 1916)).